

20th RD50 Workshop (Bari)

Thursday 31 May 2012

Detector Characterization and Simulations (09:00 - 15:30)

-Conveners: Eckhart Fretwurst; Vladimir Eremin

time	[id] title	presenter
09:00	[19] FORMATION AND ANNEALING OF INTERSTITIAL DEFECTS IN P-TYPE SILICON AND SILICON-GERMANIUM ALLOYS UNDER ELECTRON AND ALPHA-IRRADIATION	Dr MAKARENKO, Leonid
09:20	[27] Irradiation study on diodes of different silicon materials for the CMS tracker upgrade	ERFLE, Joachim
09:40	[16] Impact of proton irradiations with different particle-energies on the electrical properties of Si-diodes	NEUBUSER, Coralie
10:00	[0] Operational conditions for enhancement of collected charge via avalanche multiplication in n-on-p strip detectors	Dr VERBITSKAYA, Elena
10:20	Coffee Break	
10:50	[2] Analysis of Edge and Surface TCTs for Irradiated 3D Silicon Strip Detectors	STEWART, Graeme Douglas
11:10	[35] Characterization of Micron n-on-p ministrip sensors irradiated with 24 GeV/c protons.	PACIFICO, Nicola
11:30	[15] Charge collection studies on heavily irradiated diodes from the RD50 multiplication run	KRAMBERGER, Gregor
11:50	[7] Thin Irradiated Strip and Pixel Detectors	WEIGELL, Philipp
12:10	[43] Low cost commercial scanning TCT setup	KRAMBERGER, Gregor
12:30	[32] TCAD Simulation of irradiated Silicon radiation detector using commercial simulation products	BENOIT, Mathieu
13:00	Lunch	
14:00	[21] Electric Field Modeling by simulations with ISE-TCAD	MINANO MOYA, Mercedes
14:20	[11] Simulation of the Double Peak Effect in irradiated Sensors	EBER, Robert
14:40	[23] Isolation Characteristics of Silicon Sensors Using Simulation Approach	Dr RANJAN, Kirti
15:00	[37] Discussion - Simulation Working Group	FRETWURST, Eckhart EREMIN, Vladimir